



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-89 Plastic-Encapsulate Transistors

2SB1119 TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 500 mW ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -1 A

Collector current (Pulse)

I_{CP} : -2 A

Collector-base voltage

$V_{(BR)CBO}$: -25 V

Operating and storage junction temperature range

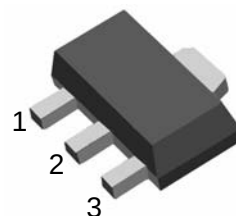
T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-89

1. BASE

2. COLLECTOR

3. EMITTER



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu A, I_E=0$	-25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-20V, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4V, I_C=0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-2V, I_C=-50mA$	100		560	
	$h_{FE(2)}$	$V_{CE}=-2V, I_C=-1A$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500mA, I_B=-50mA$			-0.7	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-500mA, I_B=-50mA$			-1.2	v
Transition frequency	f_T	$V_{CE}=-10V, I_C=-50mA$		180		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, f=1MHz$		25		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	R	S	T	U
Range	100-200	140-280	200-400	280-560
Marking	BB			